

1991 GaAs REL WORKSHOP PROGRAM
OCTOBER 20, 1991, DOUBLETREE HOTEL, MONTEREY, CALIFORNIA

SESSION I HEMT RELIABILITY K.J. Russell, Chair

RELIABILITY STUDY OF LOW-NOISE HEMTs FROM THREE MANUFACTURERS;
Y. Saito, G. Shimamoto, and T. Trihn, TRW Electronic Systems Group.

RELIABILITY OF COMMERCIAL HEMT DEVICES; S. Kayali and T. Sacco, Jet Propulsion Laboratory.

RELIABILITY STUDY ON T-SHAPED GATE HEMTs; T. Ishikawa, M. Katsumata, K. Hosogi, H. Minami, T. Kuragld, T. Katoh, S. Orisaka, K. Nishftani, and M. Otsubo, Mitsubishi Electric Corporation.

MONTE CARLO PARTICLE MODEL STUDY OF POSSIBLE FAILURE MECHANISMS IN RF RELIABILITY LIFE TESTED HEMTs, C. Moglestue, Fraunhofer Institute of Applied Solid State Physics, and W.T. Anderson, Naval Research Laboratory.

SESSION II QML BETA SITE PROGRAM W.J. Roesch, Chair

MIMIC QML PROGRAM; Daniel F. Fayette, Rome Laboratory, Griffiss Air Force Base, New York.

QML BETA SITE PANEL DISCUSSION Yashio Safto, TRW
Jim Cheevers, Texas Instruments
Bill Roesch, TriQuint Semiconductor

SESSION III MMIC AND DIGITAL IC RELIABILITY E.B. Halkim, Chair

RELIABILITY OF POWER MMICs SUBJECTED TO 2db RF COMPRESSION,
K. Decker, Texas Instruments.

FAILURE ANALYSIS OF A LIFE TESTED GaAs MMIC AMPLIFIER,
K.A. Christianson and W.T. Anderson, Naval Research Laboratory.

ACTIVE LAYER THINNING DUE TO METAL-GaAs REACTIONS IN GaAs ICs WITH Ti/Pt/Au GATE METALLIZATION; T. Hashinaga, M. Nishiguchi and H. Nishizawza, Sumitomo Electric Industries.

A NOVEL CIRCUIT DESIGN FOR GaAs THERMAL TEST DICE;
W.J. Roesch, TriQuint Semiconductor.

GaAs DIGITAL IC RELIABILITY PROGRAM;
W.E. Yamada, and K. MacWilliams, The Aerospace Corporation.

SESSION IV LIFE TESTING W.J. Koziarz, Chair

RELIABILITY INVESTIGATION OF AlInAs/GaInAs/InP HETEROJUNCTION BIPOLAR TRANSISTORS; R.J. Ferro, The Aerospace Corporation.

GaAs POWER MESFETS: DERATING AND POWER SLUMP EVALUATION;
E. Nhan, K. Chao, R. Mauer, C. Bargerion, and J. Sinsky, Johns Hopkins University APL.

INTERPRETATION OF ACCELERATED LIFE TESTS USING A TIME AND TEMPERATURE DEPENDENT MODEL OF NON-LINEAR DRIFTS IN DEVICE PARAMETERS;
J. Centanni, Hewlett-Packard Company.